

Low Power, High Slew Rate, Wideband Operational Amplifier

July 1994

Features

- This Circuit is Processed in Accordance to MIL-STD-883 and is Fully Conformant Under the Provisions of Paragraph 1.2.1.
- Low Supply Current. 8.0mA (Max)
- Low Offset Voltage. 2.0mV (Max)
- High Slew Rate. 340V/ μ s (Typ)
- Open Loop Gain. 20kV/V (Min)
- Wide Gain-Bandwidth ($A_V \geq 10$) 470MHz (Typ)
- Input Noise Voltage at 1kHz 11nV/ $\sqrt{\text{Hz}}$ (Typ)
- Lower Power Replacement for HA-2540/883, AD840

Applications

- Pulse and Video Amplifiers
- Wideband Amplifiers
- High Speed Sample-Hold Circuits
- Fast, Precise D/A Converters

Description

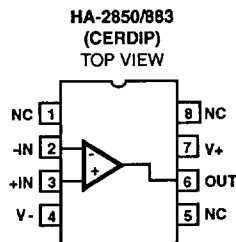
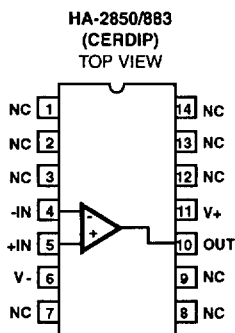
The HA-2850/883 is a wideband, high slew rate, operational amplifier featuring superior speed and bandwidth characteristics. It also features trimmed supply current, which minimizes supply current (and thus AC parameter) variation over process and temperature extremes. For example, the I_{CC} variation over the entire military temperature range is typically less than 0.5mA. Bipolar construction, coupled with dielectric isolation, delivers outstanding performance in circuits with closed loop gains ≥ 10 .

The 340V/ μ s slew rate, and 470MHz gain bandwidth product ensure high performance in video and wideband amplifier designs. Differential gain and phase are a low 0.04% and 0.04 degrees, respectively, making the HA-2850/883 ideal for video applications. A full ± 10 V output swing, high open loop gain, and outstanding AC parameters make the HA-2850/883 an excellent choice for data acquisition systems.

Ordering Information

PART NUMBER	TEMPERATURE RANGE	PACKAGE
HA1-2850/883	-55°C to +125°C	14 Lead CerDIP
HA7-2850/883	-55°C to +125°C	8 Lead CerDIP

Pinouts



Specifications HA-2850/883

Absolute Maximum Ratings

Voltage between V+ and V- Terminals 35V
 Differential Input Voltage. 6V
 Voltage at Either Input Terminal V+ to V-
 Peak Output Current ($\leq 10\%$ Duty Cycle) 50mA
 Junction Temperature (T_J) $+175^\circ\text{C}$
 Storage Temperature Range -65°C to $+150^\circ\text{C}$
 ESD Classification $<2000\text{V}$
 Lead Temperature (Soldering 10s) $+300^\circ\text{C}$

Thermal Information

Thermal Resistance θ_{JA} θ_{JC}
 14 Lead CerDIP Package 81°C/W 26°C/W
 8 Lead CerDIP Package 115°C/W 30°C/W
 Package Power Dissipation Limit at $+75^\circ\text{C}$ for $T_J \leq +175^\circ\text{C}$
 14 Lead CerDIP Package 1.23W
 8 Lead CerDIP Package 0.87W
 Package Power Dissipation Derating Factor Above $+75^\circ\text{C}$
 14 Lead CerDIP Package $12.3\text{mW}/^\circ\text{C}$
 8 Lead CerDIP Package $8.7\text{mW}/^\circ\text{C}$

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

Operating Conditions

Operating Temperature Range -55°C to $+125^\circ\text{C}$ $V_{INCM} \leq 1/2 (V+ - V-)$
 Operating Supply Voltage $\pm 12\text{V}$ to $\pm 15\text{V}$ $R_L \geq 1\text{k}\Omega$

TABLE 1. DC ELECTRICAL PERFORMANCE CHARACTERISTICS

Device Tested at: $V_{SUPPLY} = \pm 15\text{V}$, $R_{SOURCE} = 100\Omega$, $R_{LOAD} = 100\text{k}\Omega$, $V_{OUT} = 0\text{V}$, Unless Otherwise Specified.

PARAMETERS	SYMBOL	CONDITIONS	GROUP A SUBGROUP	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Input Offset Voltage	V_{IO}	$V_{CM} = 0\text{V}$	1	$+25^\circ\text{C}$	-2	2	mV
			2, 3	$+125^\circ\text{C}$, -55°C	-6	6	mV
Input Bias Current	$+I_B$	$V_{CM} = 0\text{V}$, $+R_S = 1.1\text{k}\Omega$ $-R_S = 100\Omega$	1	$+25^\circ\text{C}$	-14.5	14.5	μA
			2, 3	$+125^\circ\text{C}$, -55°C	-20	20	μA
	$-I_B$	$V_{CM} = 0\text{V}$, $+R_S = 100\Omega$ $-R_S = 1.1\text{k}\Omega$	1	$+25^\circ\text{C}$	-14.5	14.5	μA
			2, 3	$+125^\circ\text{C}$, -55°C	-20	20	μA
Input Offset Current	I_{IO}	$V_{CM} = 0\text{V}$, $+R_S = 1.1\text{k}\Omega$ $-R_S = 1.1\text{k}\Omega$	1	$+25^\circ\text{C}$	-4	4	μA
			2, 3	$+125^\circ\text{C}$, -55°C	-8	8	μA
Common Mode Range	+CMR	$V+ = 5\text{V}$, $V- = -25\text{V}$	1	$+25^\circ\text{C}$	10	-	V
			2, 3	$+125^\circ\text{C}$, -55°C	10	-	V
	-CMR	$V+ = 25\text{V}$, $V- = -5\text{V}$	1	$+25^\circ\text{C}$	-	-10	V
			2, 3	$+125^\circ\text{C}$, -55°C	-	-10	V
Large Signal Voltage Gain	$+A_{VOL}$	$V_{OUT} = 0\text{V}$ and $+10\text{V}$ $R_L = 1\text{k}\Omega$	4	$+25^\circ\text{C}$	20	-	kV/V
			5, 6	$+125^\circ\text{C}$, -55°C	10	-	kV/V
	$-A_{VOL}$	$V_{OUT} = 0\text{V}$ and -10V $R_L = 1\text{k}\Omega$	4	$+25^\circ\text{C}$	20	-	kV/V
			5, 6	$+125^\circ\text{C}$, -55°C	10	-	kV/V
Common Mode Rejection Ratio	+CMRR	$\Delta V_{CM} = 10\text{V}$, $V_{OUT} = -10\text{V}$ $V+ = 5\text{V}$, $V- = -25\text{V}$	1	$+25^\circ\text{C}$	75	-	dB
			2, 3	$+125^\circ\text{C}$, -55°C	75	-	dB
	-CMRR	$\Delta V_{CM} = -10\text{V}$, $V_{OUT} = 10\text{V}$ $V+ = 25\text{V}$, $V- = -5\text{V}$	1	$+25^\circ\text{C}$	75	-	dB
			2, 3	$+125^\circ\text{C}$, -55°C	75	-	dB

Specifications HA-2850/883

TABLE 1. DC ELECTRICAL PERFORMANCE CHARACTERISTICS (Continued)

Device Tested at: $V_{SUPPLY} = \pm 15V$, $R_{SOURCE} = 100\Omega$, $R_{LOAD} = 100k\Omega$, $V_{OUT} = 0V$, Unless Otherwise Specified.

PARAMETERS	SYMBOL	CONDITIONS	GROUP A SUBGROUP	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Output Voltage Swing	$+V_{OUT}$	$R_L = 1k\Omega$	1	+25°C	10	-	V
			2, 3	+125°C, -55°C	10	-	V
	$-V_{OUT}$	$R_L = 1k\Omega$	1	+25°C	-	-10	V
			2, 3	+125°C, -55°C	-	-10	V
Output Current	$+I_{OUT}$	$V_{OUT} = 10V$	1	+25°C	10	-	mA
			2, 3	+125°C, -55°C	10	-	mA
	$-I_{OUT}$	$V_{OUT} = -10V$	1	+25°C	-	-10	mA
			2, 3	+125°C, -55°C	-	-10	mA
Quiescent Power Supply Current	$+I_{CC}$	$V_{OUT} = 0V$, $I_{OUT} = 0mA$	1	+25°C	-	8	mA
			2, 3	+125°C, -55°C	-	8	mA
	$-I_{CC}$	$V_{OUT} = 0V$, $I_{OUT} = 0mA$	1	+25°C	-8	-	mA
			2, 3	+125°C, -55°C	-8	-	mA
Power Supply Rejection Ratio	+PSRR	$\Delta V_{SUP} = 10V$ $V_+ = 10V$, $V_- = -15V$ $V_+ = 20V$, $V_- = -15V$	1	+25°C	75	-	dB
			2, 3	+125°C, -55°C	75	-	dB
	-PSRR	$\Delta V_{SUP} = 10V$ $V_+ = 15V$, $V_- = -10V$ $V_+ = 15V$, $V_- = -20V$	1	+25°C	75	-	dB
			2, 3	+125°C, -55°C	75	-	dB

TABLE 2. AC ELECTRICAL PERFORMANCE CHARACTERISTICS

Table 2 Intentionally Left Blank. See A.C. Specifications in Table 3

Specifications HA-2850/883

TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS

Device Characterized at: $V_{SUPPLY} = \pm 15V$, $R_{SOURCE} = 50\Omega$, $R_{LOAD} = 1k\Omega$, $C_L \leq 10pF$, $A_V = +10V/V$, Unless Otherwise Specified.

PARAMETERS	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Gain Bandwidth Product	GBWP	$V_O = 200mV$, $f_O = 5MHz$	1	+25°C	400	-	MHz
		$V_O = 200mV$, $f_O = 45MHz$	1	+25°C	350	-	MHz
Slew Rate	+SR	$V_O = -5V$ to $+5V$	1, 4	+25°C	300	-	V/ μs
	-SR	$V_O = +5V$ to $-5V$	1, 4	+25°C	300	-	V/ μs
Full Power Bandwidth	FPBW	$V_{PEAK} = 10V$	1, 2	+25°C	4.8	-	MHz
Rise and Fall Time	T_R	$V_O = 0V$ to $+200mV$	1, 4	+25°C	-	15	ns
	T_F	$V_O = 0V$ to $-200mV$	1, 4	+25°C	-	15	ns
Minimum Closed Loop Stable Gain	CLSG	$R_L = 1k\Omega$, $C_L \leq 10pF$	1	-55°C to +125°C	10	-	V/V
Overshoot	+OS	$V_O = 0V$ to $+200mV$	1	+25°C	-	30	%
	-OS	$V_O = 0V$ to $-200mV$	1	+25°C	-	30	%
Open Loop Output Resistance	R_{OUT}	$V_{OUT} = 0V$	1	+25°C	-	60	Ω
Quiescent Power Consumption	PC	$V_{OUT} = 0V$, $I_{OUT} = 0mA$	1, 3	-55°C to +125°C	-	240	mW

NOTES:

- Parameters listed in Table 3 are controlled via design or process parameters and are not directly tested at final production. These parameters are lab characterized upon initial design release, or upon design changes. These parameters are guaranteed by characterization based upon data from multiple production runs which reflect lot to lot and within lot variation.
- Full Power Bandwidth guarantee based on Slew Rate measurement using $FPBW = \text{Slew Rate}/(2\pi V_{PEAK})$.
- Quiescent Power Consumption based upon Quiescent Supply Current test maximum. (No load on outputs.)
- Measured between 10% and 90% points.

TABLE 4. ELECTRICAL TEST REQUIREMENTS

MIL-STD-883 TEST REQUIREMENTS	SUBGROUPS (SEE TABLE 1)
Interim Electrical Parameters (Pre Burn-In)	1
Final Electrical Test Parameters	1 (Note 1), 2, 3, 4, 5, 6
Group A Test Requirements	1, 2, 3, 4, 5, 6
Groups C and D Endpoints	1

NOTE:

- PDA applies to Subgroup 1 only.

Die Characteristics**DIE DIMENSIONS:**65 x 52 x 19 mils $\pm$ 1 mils1650 x 1310 x 483 μ m $\pm$ 25.4 μ m**METALLIZATION:**

Type: Al, 1% Cu

Thickness: 16k $\text{\AA}$ $\pm$ 2k $\text{\AA}$ **GLASSIVATION:**

Type: Nitride over Silox

Silox Thickness: 12k $\text{\AA}$ $\pm$ 2k $\text{\AA}$ Nitride Thickness: 3.5k $\text{\AA}$ $\pm$ 1.5k $\text{\AA}$ **WORST CASE CURRENT DENSITY:**0.7 x 10⁵ A/cm² at 1.8mA**SUBSTRATE POTENTIAL (Powered Up): V-****TRANSISTOR COUNT: 34****PROCESS: Bipolar Dielectric Isolation*****Metallization Mask Layout***